

N-Channel Enhancement Mode MOSFET

TDM3508

DESCRIPTION

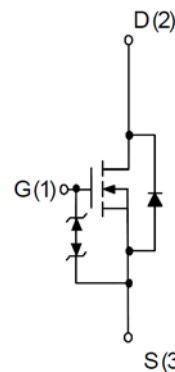
The TDM3508 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

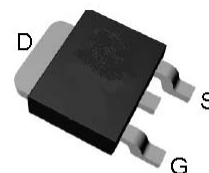
- RDS(ON) < 12mΩ @ VGS=4.5V
RDS(ON) < 7.5mΩ @ VGS=10V
- High Power and current handling capability
- Lead free product is available
- ESD protection
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



N-Channel MOSFET



Top View of TO-252-2

ABSOLUTE MAXIMUM RATINGS($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current @ Continuous	I _D (T _C =25°C)	68	A
	I _D (T _C =100°C)	40	A
Drain Current @ Current-Pulsed (Note 1)	I _{DM} (T _C =25°C)	120	A
Maximum Power Dissipation	P _D (T _C =25°C)	50	W
	P _D (T _C =100°C)	20	W
Drain Current @ Continuous	I _D (T _A =25°C)	17	A
	I _D (T _A =70°C)	13.5	A
Maximum Power Dissipation	P _D (T _A =25°C)	2.5	W
	P _D (T _A =70°C)	1.6	W
Thermal Resistance-Junction to Ambient	R _{θJA}	50	°C/W
Avalanche Current, Single pulse	I _{AS} (L=0.1mH)	20	A
Avalanche Energy, Single pulse	E _{AS} (L=0.1mH)	20	mJ
Maximum Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 To 150	°C

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ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

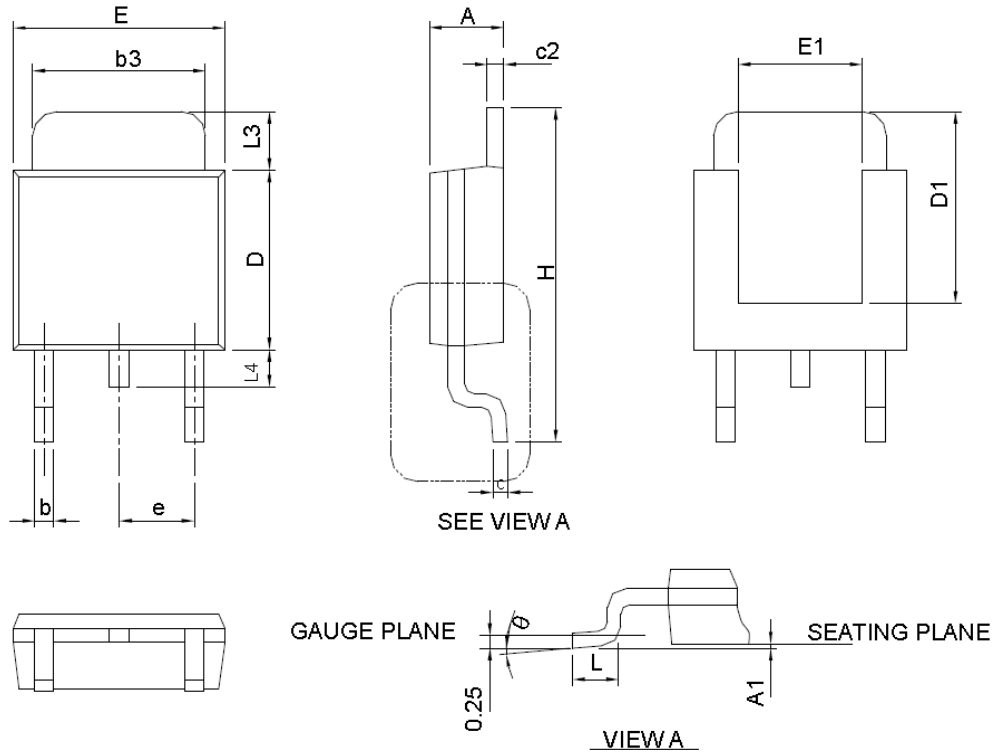
Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 10	μA
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.4	1.7	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=10A$	-	8.8	12	$m\Omega$
		$V_{GS}=10V, I_D=15A$	-	6.45	7.5	$m\Omega$
		$T_J=100^{\circ}C$	-	8.8	-	$m\Omega$
DYNAMIC CHARACTERISTICS (Note 4)						
Gate Resistance	R_G	$V_{DS}=0V, V_{GS}=0V, F=1.0MHz$	-	1.6	2.5	Ω
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, F=1.0MHz$	-	780	1100	PF
Output Capacitance	C_{oss}		-	510	-	PF
Reverse Transfer Capacitance	C_{rss}		-	39	-	PF
SWITCHING CHARACTERISTICS (Note 3)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=15V, R_L=15\Omega, V_{GEN}=10V, R_G=1\Omega$ $I_D=1A$	-	11	-	nS
Turn-on Rise Time	t_r		-	8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	19.6	-	nS
Turn-Off Fall Time	t_f		-	17	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=15A, V_{GS}=4.5V$	-	5.8	-	nC
Gate-Source Charge	Q_{gs}		-	3	-	nC
Gate-Drain Charge	Q_{gd}		-	1.5	-	nC
Body Diode Reverse Recovery Time	T_{rr}	$I_F=5A, di/dt=100A/\mu s$	-	25	-	nS
Body Diode Reverse Recovery Charge	Q_{rr}		-	11.8	-	nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 2)	V_{SD}	$V_{GS}=0V, I_S=10A$	-	0.8	1.1	V

NOTES:

1. Pulse width limited by max. junction temperature.
2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
3. Guaranteed by design, not subject to production testing

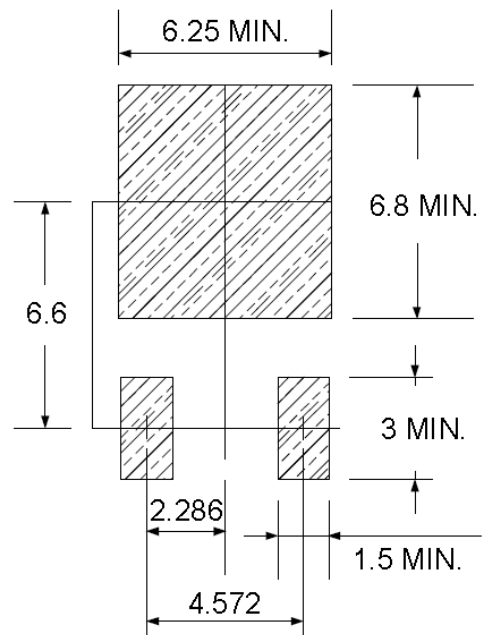
Package Information

TO252-2 Package



DIMENSIONS	TO-252-2			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	-	0.13	-	0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4	-	1.02	-	0.040
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



UNIT: mm

Design Notes